

PN2222, PN2222A

PN2222A is a Preferred Device

General Purpose Transistors

NPN Silicon

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage PN2222 PN2222A	V_{CEO}	30 40	Vdc
Collector-Base Voltage PN2222 PN2222A	V_{CBO}	60 75	Vdc
Emitter-Base Voltage PN2222 PN2222A	V_{EBO}	5.0 6.0	Vdc
Collector Current – Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

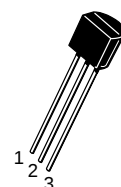
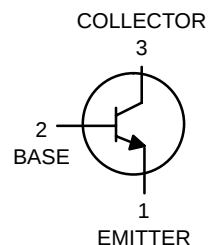
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$



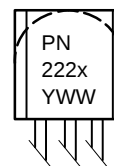
ON Semiconductor™

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TO-92
CASE 29
STYLE 1

MARKING DIAGRAM



PN222x= Device Code
x = 2 or A
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
PN2222	TO-92	5000 Units/Box
PN2222A	TO-92	5000 Units/Box
PN2222ARLRA	TO-92	2000/Tape & Reel
PN2222ARLRM	TO-92	2000/Ammo Pack
PN2222ARLRP	TO-92	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

PN2222, PN2222A

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	PN2222 PN2222A	V _{(BR)CEO}	30 40	– –	Vdc
Collector–Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	PN2222 PN2222A	V _{(BR)CBO}	60 75	– –	Vdc
Emitter–Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	PN2222 PN2222A	V _{(BR)EBO}	5.0 6.0	– –	Vdc
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	PN2222A	I _{CEX}	–	10	nAdc
Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0) (V _{CB} = 60 Vdc, I _E = 0) (V _{CB} = 50 Vdc, I _E = 0, T _A = 125°C) (V _{CB} = 50 Vdc, I _E = 0, T _A = 125°C)	PN2222 PN2222A PN2222 PN2222A	I _{CBO}	– – – –	0.01 0.01 10 10	μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)	PN2222A	I _{EBO}	–	100	nAdc
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB(off)} = 3.0 Vdc)	PN2222A	I _{BL}	–	20	nAdc

ON CHARACTERISTICS

DC Current Gain (I _C = 0.1 mAdc, V _{CE} = 10 Vdc) (I _C = 1.0 mAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 10 Vdc) (I _C = 10 mAdc, V _{CE} = 10 Vdc, T _A = –55°C) (I _C = 150 mAdc, V _{CE} = 10 Vdc) (Note 1.) (I _C = 150 mAdc, V _{CE} = 1.0 Vdc) (Note 1.) (I _C = 500 mAdc, V _{CE} = 10 Vdc) (Note 1.)	PN2222A only PN2222 PN2222A	h _{FE}	35 50 75 35 100 50 30 40	– – – – 300 – – –	–
Collector–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	PN2222 PN2222A PN2222 PN2222A	V _{CE(sat)}	– – – –	0.4 0.3 1.6 1.0	Vdc
Base–Emitter Saturation Voltage (Note 1.) (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	PN2222 PN2222A PN2222 PN2222A	V _{BE(sat)}	– 0.6 – –	1.3 1.2 2.6 2.0	Vdc

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

PN2222, PN2222A

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain – Bandwidth Product (Note 2.) ($I_C = 20\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	250 300	– –	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	8.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	– –	30 25	pF
Input Impedance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	2.0 0.25	8.0 1.25	k Ω
Voltage Feedback Ratio ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{re}	– –	8.0 4.0	$\times 10^{-4}$
Small-Signal Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	50 75	300 375	–
Output Admittance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant ($I_E = 20\text{ mAdc}$, $V_{CB} = 20\text{ Vdc}$, $f = 31.8\text{ MHz}$)	$r_b'C_c$	–	150	ps
Noise Figure ($I_C = 100\text{ }\mu\text{Adc}$, $V_{CE} = 10\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	NF	–	4.0	dB

SWITCHING CHARACTERISTICS PN2222A only

Delay Time	$(V_{CC} = 30\text{ Vdc}$, $V_{BE(off)} = -0.5\text{ Vdc}$, $I_C = 150\text{ mAdc}$, $I_{B1} = 15\text{ mAdc}$) (Figure 1)	t_d	–	10	ns
Rise Time		t_r	–	25	ns
Storage Time	$(V_{CC} = 30\text{ Vdc}$, $I_C = 150\text{ mAdc}$, $I_{B1} = I_{B2} = 15\text{ mAdc}$) (Figure 2)	t_s	–	225	ns
Fall Time		t_f	–	60	ns

2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

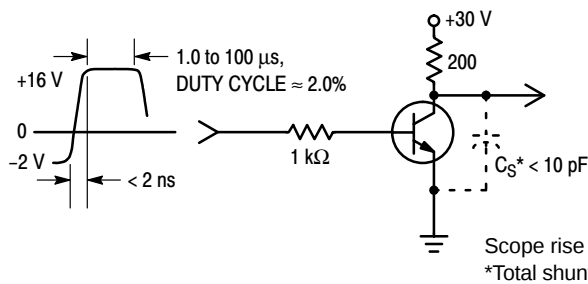


Figure 1. Turn-On Time

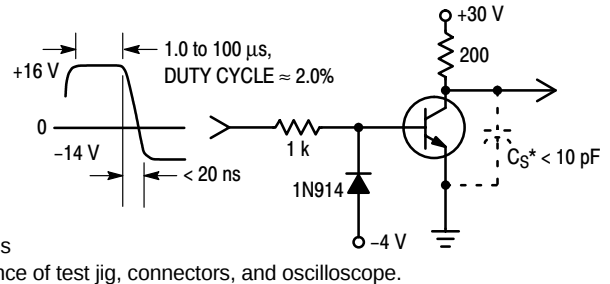


Figure 2. Turn-Off Time

PN2222, PN2222A

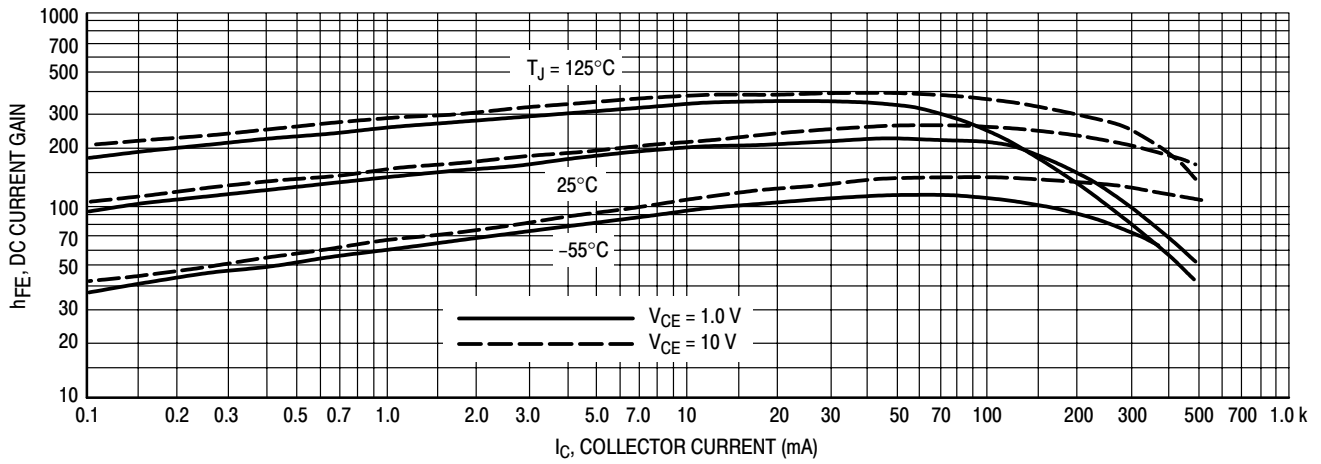


Figure 3. DC Current Gain

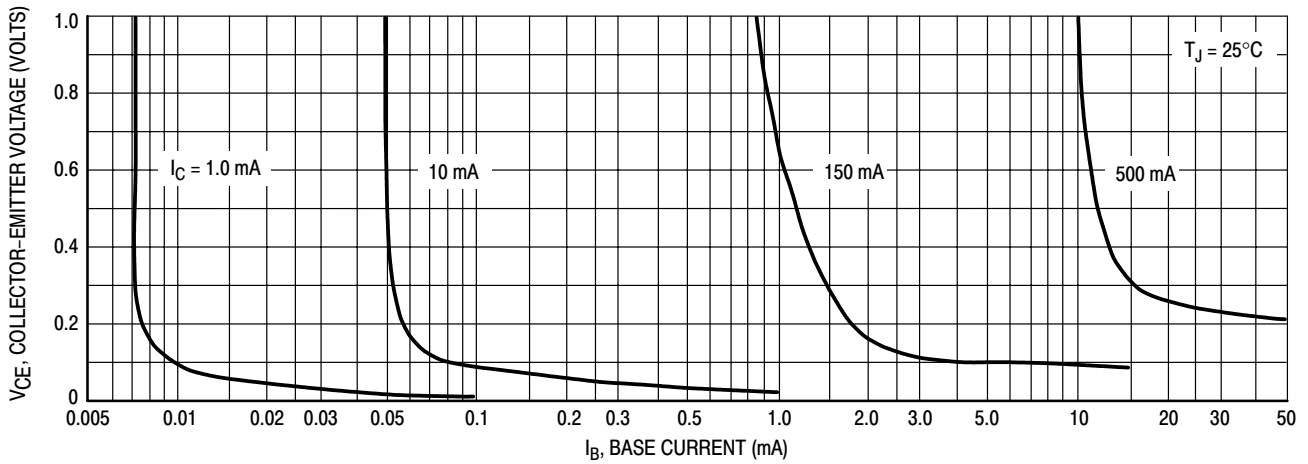


Figure 4. Collector Saturation Region

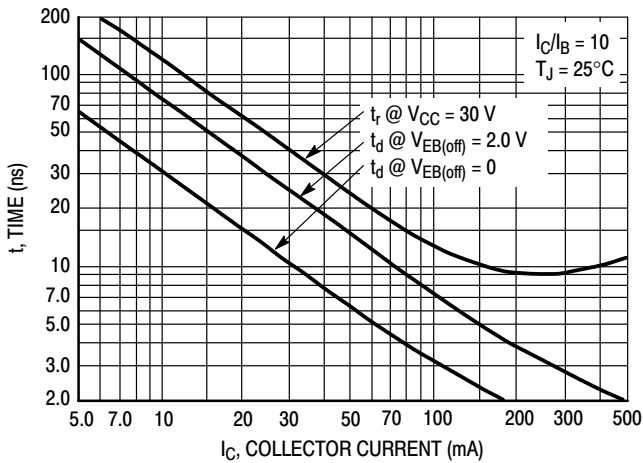


Figure 5. Turn-On Time

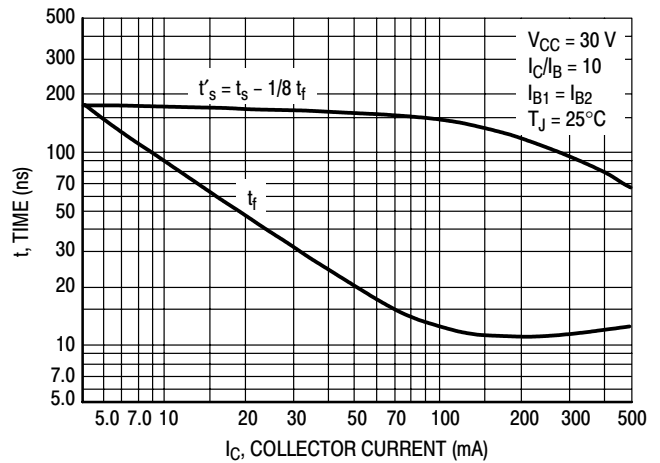


Figure 6. Turn-Off Time

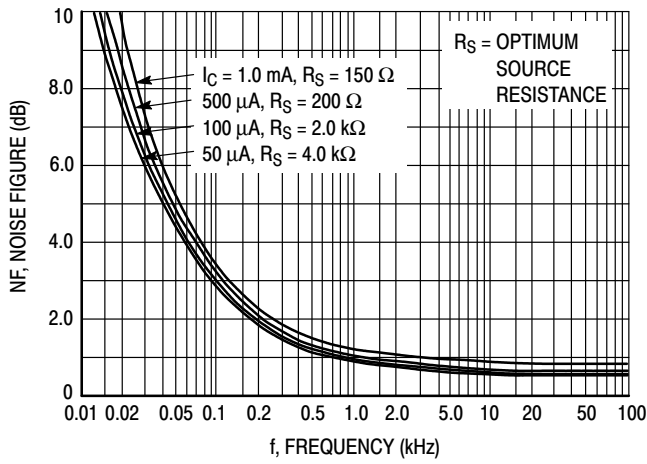


Figure 7. Frequency Effects

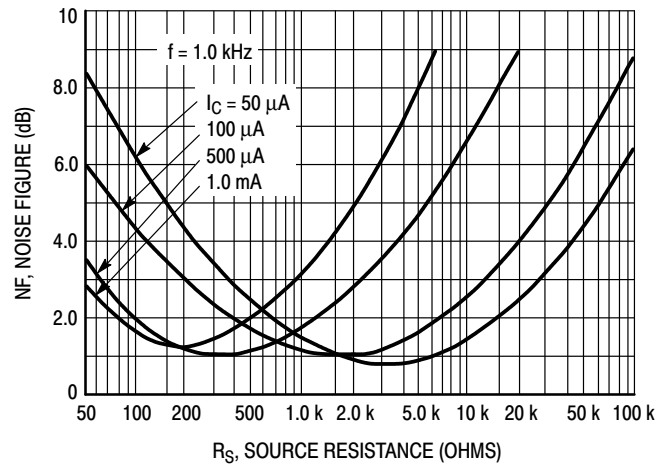


Figure 8. Source Resistance Effects

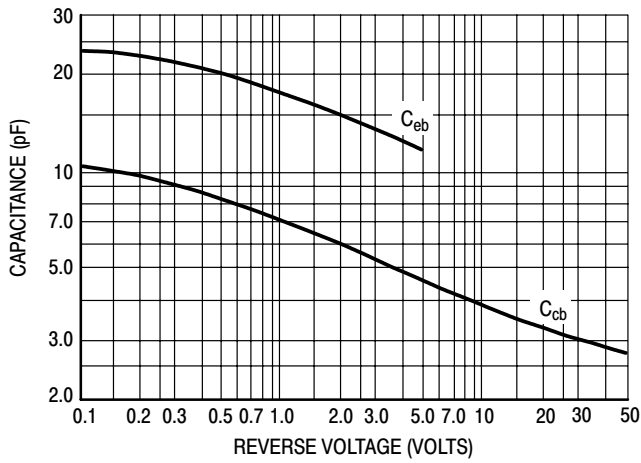


Figure 9. Capacitances

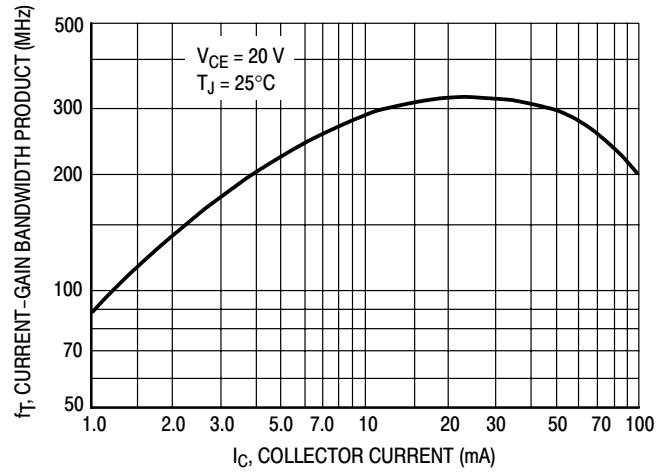


Figure 10. Current-Gain Bandwidth Product

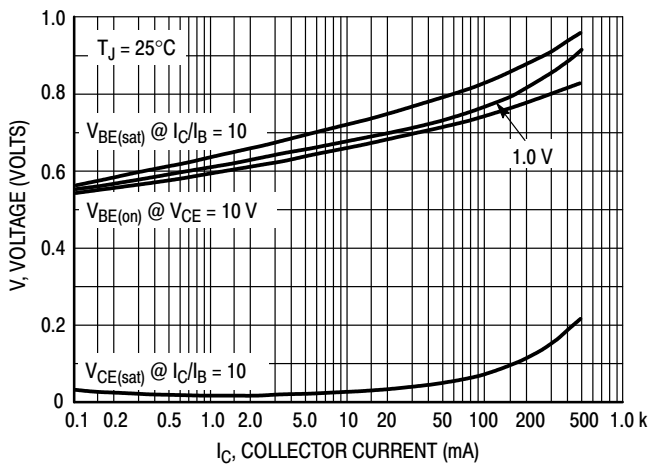


Figure 11. "On" Voltages

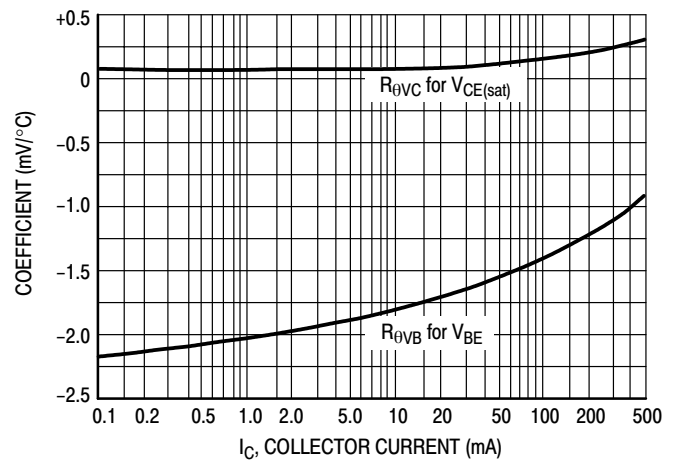
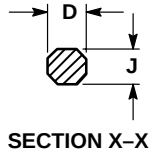
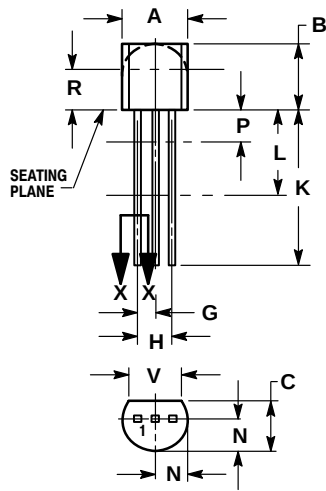


Figure 12. Temperature Coefficients

PN2222, PN2222A

PACKAGE DIMENSIONS

TO-92
TO-226AA
CASE 29-11
ISSUE AL



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:

- PIN 1. EMITTER
- BASE
- COLLECTOR

Notes

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